

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error	Errors
1	BRS	32	nano\$ with wide with bandgap and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:08			0
2	BRS	35	nano\$ with wide with bandgap	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 23:43			0
3	BRS	22	nano\$ with wide with bandgap and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 23:44			0
4	BRS	22	nano\$ with wide with bandgap and beam and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 23:46			0
5	BRS	2	energy with wide with bandgap and beam and second near	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 23:44			0
6	BRS	17	energy with wide with bandgap and beam and energy and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 23:54			0
7	BRS	4	heat\$4 with wide with bandgap and beam and energy and heat\$4 with (source or drain or gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 23:58			0
8	BRS	3	nano\$ with wide with bandgap and beam and energy and heat\$4 and source and drain and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:03			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Errors
9	BRS	3	nano\$ with wide with bandgap and heat\$4 and source and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:06		0
10	BRS	1	drain and gate nano\$ with wide with bandgap and heat\$4 with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:05		0
11	BRS	4	semiconduct\$ with wide with bandgap and source and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:12		0
12	BRS	11	drain and gate 4697197.URPN.	USPAT	2004/08/12 00:08		0
13	BRS	53	nano\$ and wide with bandgap and source and drain and gate and heat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:13		0
14	BRS	51	nano\$ and wide with bandgap and source and drain and gate and heat\$5 and dop\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:13		0
15	BRS	49	nano\$ and wide with bandgap and source and drain and gate and heat\$5 and dop\$5 and semiconduct\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:19		0
16	BRS	19	nano\$ and wide with bandgap and source and (drain or gate) with heat\$5 and dop\$5 and semiconduct\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:21		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Info
17	BRS	2	nano\$ and wide with bandgap and source and (drain or gate) with heat\$5 and dop\$5 and semiconduct\$5 and (single near crystal or monocrystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:30		0
18	BRS	18	nano\$ and wide with bandgap and source and drain and gate and heat\$5 and dop\$5 and semiconduct\$5 and (single near crystal or monocrystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:32		0
19	BRS	15	nano\$ and wide with bandgap and source and drain and gate and heat\$5 and dop\$5 and semiconduct\$5 and (single near crystal or monocrystal) and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:33		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error	Errors
20	BRS	10	nano\$ and wide with bandgap and source and drain and gate and heat\$5 and dop\$5 and semiconduct\$5 and (single near crystal or monocrystal) and (laser near beam or electron near beam or charg\$4 near particl\$4 or ion near beam or electromagnet\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:36			0
21	BRS	29	nano\$ with wide adj bandgap and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 18:25			0
22	BRS	3	nano\$ with wide adj bandgap and semiconductor and (heat\$5 or thermal) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 18:27			0
23	BRS	24	nano\$ with wide adj bandgap and semiconductor and (heat\$5 or thermal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 18:28			0
24	BRS	0	wide with bandgap with irradiat\$6 with laser and nano\$8 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:10			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Errors
32	BRS	50	wide with (bandgap or band with gap) and irradiat\$ with laser and nano\$8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:30		0
33	BRS	20	wide with (bandgap or band with gap) and irradiat\$ with laser and nano\$8 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:38		0
34	BRS	31	wide with (bandgap or band with gap) and laser with nano\$8 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:46		0
35	BRS	0	wide with (bandgap or band with gap) near (laser or beam or heat\$6 or eb or electron near beam or thermal\$4) with nano\$8 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:48		0
36	BRS	0	wide with (bandgap or band with gap) near (laser or beam or heat\$6 or eb or electron near beam or thermal\$4) and nano\$ and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:49		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error	Position
37	BRS	0	wide with (bandgap or band with gap) near (laser or beam or heat\$6 or eb or electron near beam or thermal\$4) and nano\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:49			0
38	BRS	167	wide with (bandgap or band with gap) with (laser or beam or heat\$6 or eb or electron near beam or thermal\$4) and nano\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:49			0
39	BRS	2	wide with (bandgap or band with gap) with (laser or beam or heat\$6 or eb or electron near beam or thermal\$4) and nano\$ with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:50			0
40	BRS	54	wide with (bandgap or band with gap) and (laser or beam or heat\$6 or eb or electron near beam or thermal\$4) and nano\$ with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 23:29			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error
41	BRS	0	wide with (bandgap or band with gap) near (laser or beam or heat\$6 or eb or electron near beam or thermal\$4) and nano\$ with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 23:29		0
42	BRS	0	wide with (bandgap or band with gap) near (laser or beam or heat\$6 or eb or electron near beam or thermal\$4) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 23:30		0
43	BRS	258	wide with (bandgap or band with gap) with (laser or beam or heat\$6 or eb or electron near beam or thermal\$4) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 23:30		0
44	BRS	17	wide with (bandgap or band with gap) with second with (laser or beam or heat\$6 or eb or electron near beam or thermal\$4) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 23:31		0